

2SD2441

Silicon NPN epitaxial planer type

For low-frequency output amplification

■ Features

- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	10	V
Collector to emitter voltage	V_{CEO}	10	V
Emitter to base voltage	V_{EBO}	7	V
Peak collector current	I_{CP}	2	A
Collector current	I_C	1.5	A
Collector power dissipation	P_C^*	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

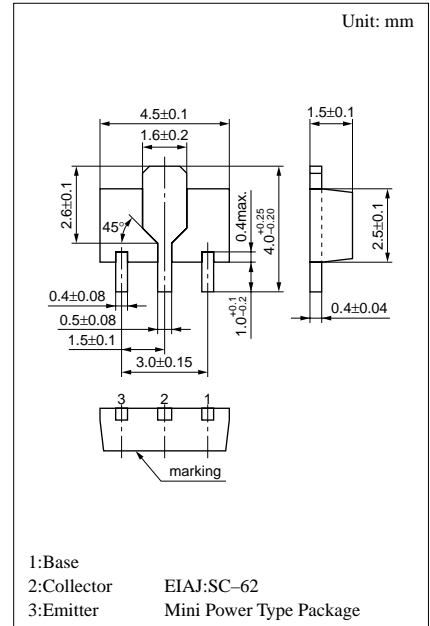
* Printed circuit board: Copper foil area of 1cm² or more, and the board thickness of 1.7mm for the collector portion

■ Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 7V, I_E = 0$			1	μA
Collector to base voltage	V_{CBO}	$I_C = 10\mu A, I_E = 0$	10			V
Collector to emitter voltage	V_{CEO}	$I_C = 1mA, I_B = 0$	10			V
Emitter to base voltage	V_{EBO}	$I_E = 10\mu A, I_C = 0$	7			V
Forward current transfer ratio	h_{FE}	$V_{CE} = 1V, I_C = 400mA^{*2}$	200		700	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 1A, I_B = 25mA^{*2}$		0.17	0.25	V
Transition frequency	f_T	$V_{CB} = 60V, I_E = -50mA, f = 200MHz$		190		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		50		pF
Forward voltage	V_F^{*1}	$I_F = 500mA$			1.3	V

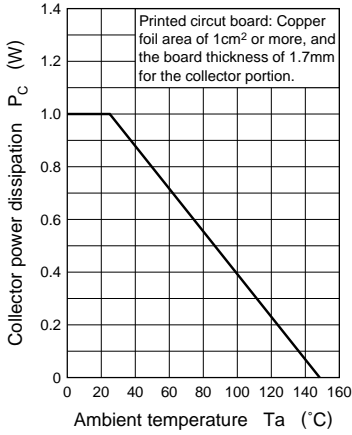
*1 Applicable to the built-in diode.

*2 Pulse measurement

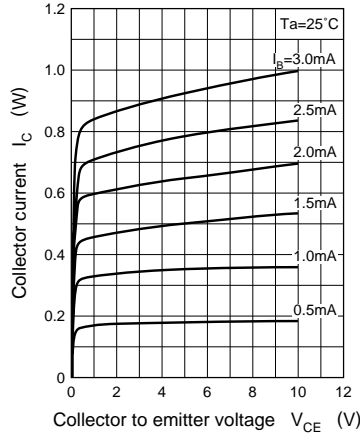


Marking symbol : 1V

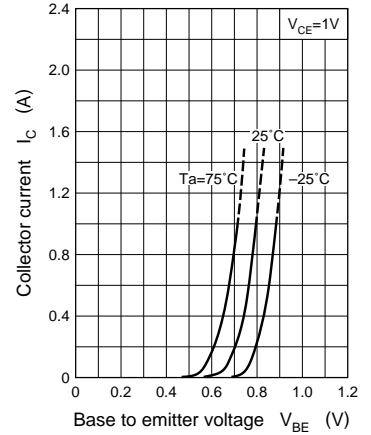
$P_C - T_a$



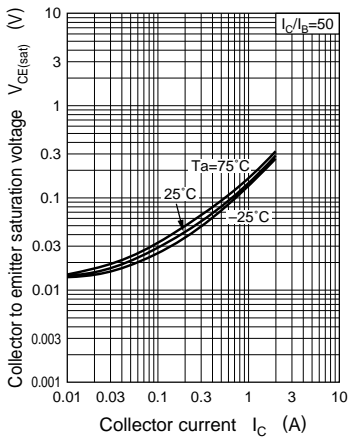
$I_C - V_{CE}$



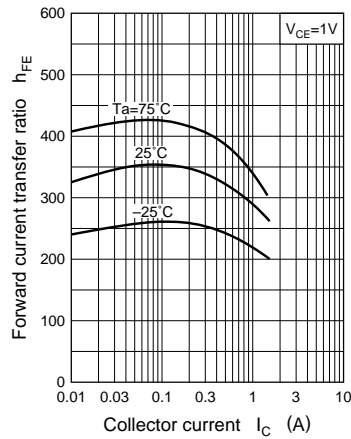
$I_C - V_{BE}$



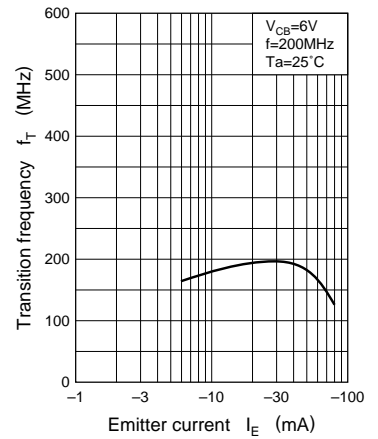
$V_{CE(sat)} - I_C$



$h_{FE} - I_C$



$f_T - I_E$



$C_{ob} - V_{CB}$

